# MBD301G, MMBD301LT1G, MMBD301LT3G, SMMBD301LT3G

# **Silicon Hot-Carrier Diodes**

# **Schottky Barrier Diodes**

These devices are designed primarily for high-efficiency UHF and VHF detector applications. They are readily adaptable to many other fast switching RF and digital applications. They are supplied in an inexpensive plastic package for low-cost, high-volume consumer and industrial/commercial requirements. They are also available in a Surface Mount package.

#### **Features**

- Extremely Low Minority Carrier Lifetime 15 ps (Typ)
- Very Low Capacitance 1.5 pF (Max) @  $V_R = 15 \text{ V}$
- Low Reverse Leakage I<sub>R</sub> = 13 nAdc (Typ) MBD301, MMBD301
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Reverse Voltage	V <sub>R</sub>	30	V
Forward Current (DC)	ΙF	200 (Max)	mA
Total Device Dissipation  (a) T <sub>A</sub> = 25°C  MBD301G  MMBD301LT1G, MMBD301LT3G,  SMMBD301LT3G  Derate above 25°C  MBD301G  MMBD301LT1G, MMBD301LT3G,  SMMBD301LT3G	P <sub>F</sub>	280 200 2.8 2.0	MW mW/°C
Operating Junction Temperature Range	TJ	-55 to +125	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	°C

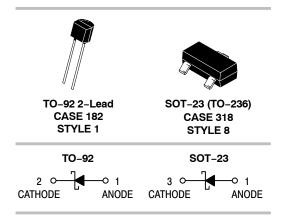
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



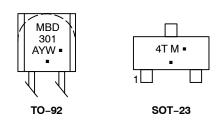
# ON Semiconductor®

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# 30 VOLTS SILICON HOT-CARRIER DETECTOR AND SWITCHING DIODES



# **MARKING DIAGRAMS**



A = Assembly Location

′ = Year

W = Work Week

4T = Device Code (SOT-23)

M = Date Code\*

= Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

# MBD301G, MMBD301LT1G, MMBD301LT3G, SMMBD301LT3G

# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25$ °C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Breakdown Voltage (I <sub>R</sub> = 10 μA)	V <sub>(BR)R</sub>	30	-	-	V
Total Capacitance (V <sub>R</sub> = 15 V, f = 1.0 MHz) Figure 1	C <sub>T</sub>	-	0.9	1.5	pF
Reverse Leakage (V <sub>R</sub> = 25 V) Figure 3	I <sub>R</sub>	-	13	200	nAdc
Forward Voltage (I <sub>F</sub> = 1.0 mAdc) Figure 4	V <sub>F</sub>	-	0.38	0.45	Vdc
Forward Voltage (I <sub>F</sub> = 10 mAdc) Figure 4	V <sub>F</sub>	-	0.52	0.6	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MBD301G	TO-92 (Pb-Free)	5,000 Units / Bulk
MMBD301LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBD301LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SMMBD301LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MBD301G, MMBD301LT1G, MMBD301LT3G, SMMBD301LT3G

# TYPICAL ELECTRICAL CHARACTERISTICS

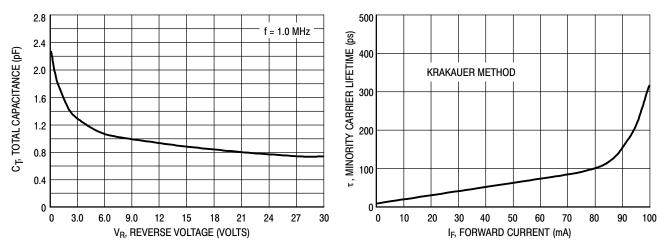


Figure 1. Total Capacitance

Figure 2. Minority Carrier Lifetime

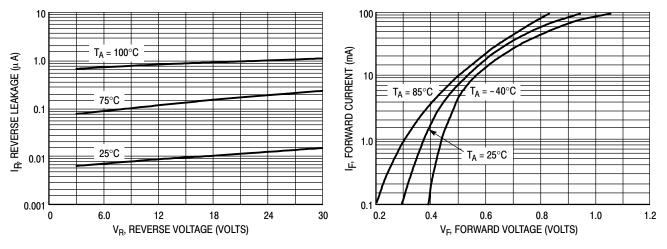


Figure 3. Reverse Leakage

Figure 4. Forward Voltage

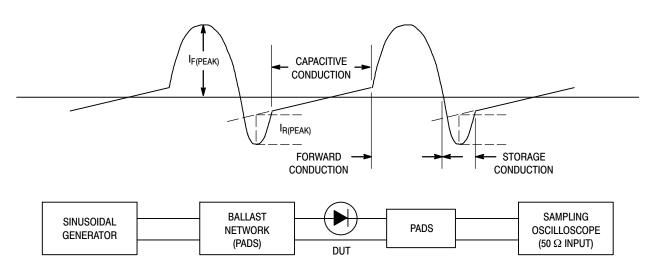


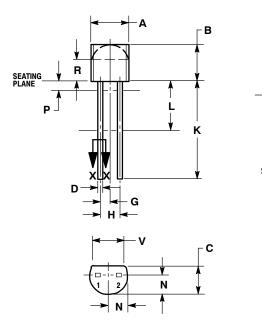
Figure 5. Krakauer Method of Measuring Lifetime



TO-92 (TO-226) CASE 182-06 **ISSUE L** 

**DATE 04/18/1998** 







**SECTION X-X** 

- OTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. CONTOUR OF PACKAGE BEYOND ZONE R IS UNCONTROLLED.
  4. LEAD DIMENSION IS UNCONTROLLED IN P AND

- BEYOND DIMENSION K MINIMUM.

	INCHES		INCHES MILLII		IETERS
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.21	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.021	0.407	0.533	
G	0.050 BSC		1.27 BSC		
Н	0.100 BSC		2.54 BSC		
L	0.014	0.016	0.36	0.41	
K	0.500	-	12.70		
L	0.250	-	6.35		
N	0.080	0.105	2.03	2.66	
Р		0.050		1.27	
R	0.115		2.93		
٧	0.135		3.43		

STYLE 1: PIN 1. ANODE STYLE 2: PIN 1. CATHODE STYLE 3: PIN 1. MAIN TERMINAL 1 STYLE 5: PIN 1. INPUT STYLE 4: CANCELLED 2. CATHODE 2. ANODE 2. MAIN TERMINAL 2 2. OUTPUT

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SOT-23 (TO-236) CASE 318-08 **ISSUE AS** 

**DATE 30 JAN 2018** 

# SCALE 4:1 D - 3X b **TOP VIEW**







#### **RECOMMENDED SOLDERING FOOTPRINT**



DIMENSIONS: MILLIMETERS

3. ANODE

#### NOTES:

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
  MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	O٥		10°	O۰		10°

#### **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	ı	
STYLE 9:	STYLE 10:	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN		PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE		2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE		3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE		PIN 1. NO CONNECTION	I PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE		2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE		3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE				

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